

2SK1613

Silicon N-Channel Power F-MOS FET

■ Features

- High avalanche energy capacity
- V_{GS} : 30V guaranteed
- Low $R_{DS(on)}$, high-speed switching characteristic

■ Applications

- High-speed switching (switching power supply)
- For high-frequency power amplification

■ Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rated	Unit
Drain to Source breakdown voltage	V_{DSS}	900	V
Gate to Source voltage	V_{GSS}	± 30	V
Drain current	DC	I_D	± 5 A
	Pulse	I_{DP}	± 10 A
Avalanche energy capacity	EAS*	45	mJ
Allowable power dissipation	$T_C = 25^\circ C$	P_D	100 W
	$T_a = 25^\circ C$		2.5 W
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse

■ Electrical Characteristics ($T_C = 25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 720V, V_{GS} = 0$			0.1	mA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0$			± 1	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1mA, V_{GS} = 0$	900			V	
Avalanche energy capacity	EAS*	$L = 3.6mH, I_D = 5A, V_{DD} = 50V$	45			mJ	
Gate threshold voltage	V_{th}	$V_{DS} = 25V, I_D = 1mA$	2		5	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$		2	2.8	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25V, I_D = 3A$	1.5	3.5		S	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$		1400		pF	
Output capacitance (Common Source)	C_{oss}				140		pF
Reverse transfer capacitance (Common Source)	C_{rss}				60		pF
Turn-on time	t_{on}	$V_{GS} = 10V, I_D = 3A$ $V_{DD} = 200V, R_L = 66\Omega$		90		ns	
Fall time	t_f				60		ns
Turn-off time (delay time)	$t_{d(off)}$				170		ns

* Avalanche energy capacity test circuit



